

## Supporting Information

### Charge mobility enhancement for diketopyrrolopyrrole-based conjugated polymers by partial replacement of branching alkyl chains with linear ones

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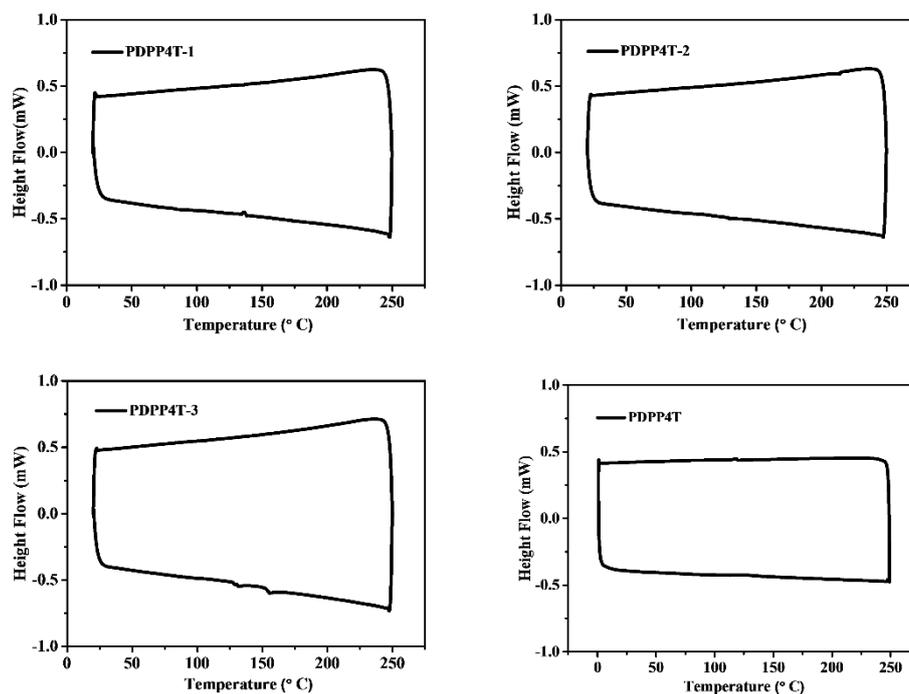
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## 1. Characterization techniques

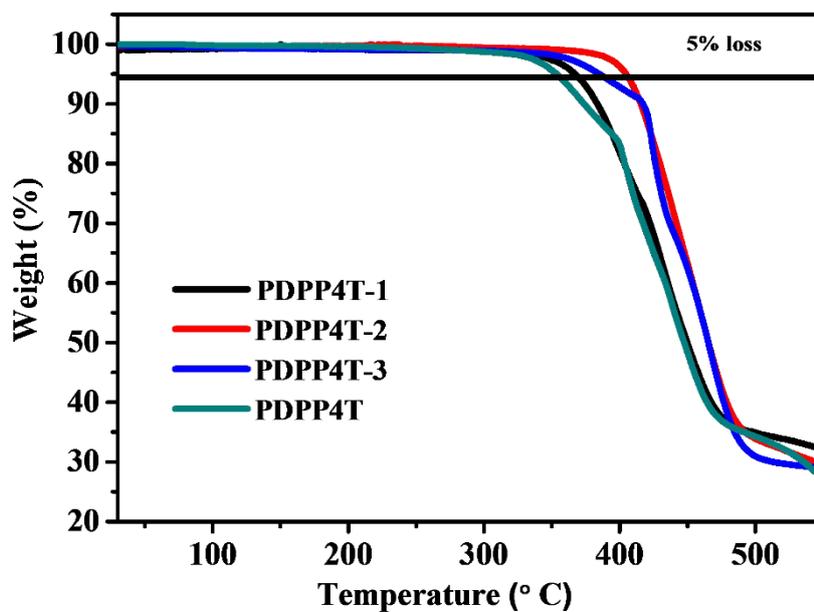
$^1\text{H}$  NMR and  $^{13}\text{C}$  NMR spectra were recorded on Bruker AVANCE III 500, 400, and 100 MHz spectrometers. Elemental analysis was measured with a Carlo Erba model 1160 elemental analyzer. UV-vis absorption spectra were measured with JASCO V-570 UV-vis spectrophotometer. Gel permeation chromatography (GPC) analysis was performed on an PL-GPC 220 high-temperature chromatograph at  $150^\circ\text{C}$  equipped with a IR5 detector; polystyrene was used as the calibration standard and 1,2,4-trichlorobenzene as eluent (the flow rate was 1.0 mL/min). Thermogravimetric analysis (TGA) were performed on a Shimadzu DTG-60 instruments under a dry nitrogen flow with the temperature from room temperature to  $550^\circ\text{C}$  ( $10^\circ\text{C}/\text{min}$ ). For differential scanning calorimetry (DSC) measurements  $\sim 5$  mg of the sample was used and the measurement was conducted under nitrogen at a scan rate of  $10^\circ\text{C}/\text{min}$  with a DSC-Q2000 instrument. Cyclic voltammetric measurements were carried out in a conventional three-electrode cell using a glassy carbon working electrode, a Pt counter electrode, and a Ag/AgCl (saturated KCl) reference electrode on a computer-controlled CHI660C instruments at ambient temperature;  $n\text{-Bu}_4\text{NPF}_6$  (0.1 M) was used as the supporting electrolyte. The onset oxidation and reduction potentials were presented by reference to the redox potential of ferrocene/ferrocenium ( $\text{Fc}/\text{Fc}^+$ ). Atomic-force microscopy images of thin films of polymers were taken by using a Digital Instruments Nanoscope V atomic force microscope operated in tapping mode with a Nanoscope V instrument in air. The GIXRD data of thin films of polymers were obtained at Beijing Synchrotron Radiation Facility, 1W1A.

## 2. Differential scanning calorimetry (DSC) curves



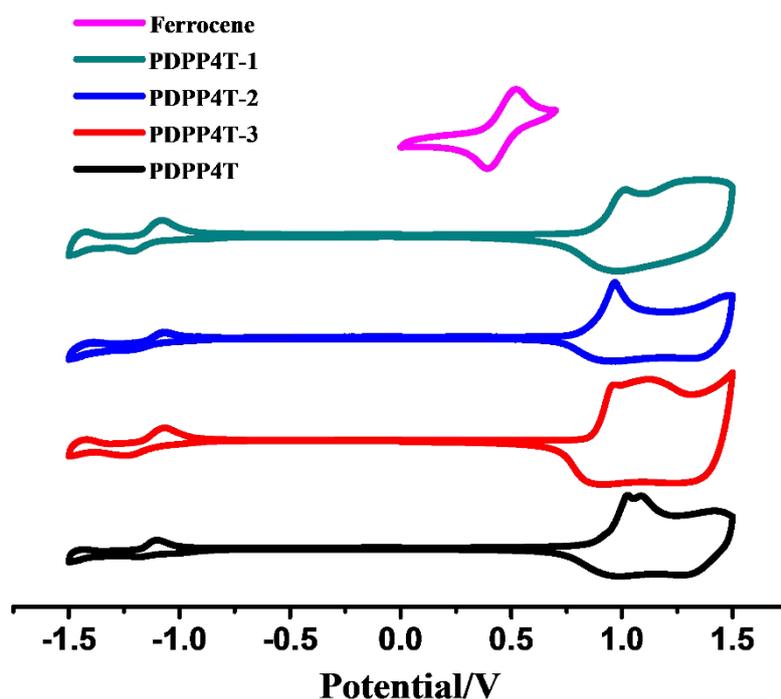
**Figure S1** DSC curves of PDPP4T-1, PDPP4T-2, PDPP4T-3, and PDPP4T recorded at a heating and cooling rate (25-250 °C) of 10 °C/min under nitrogen.

## 3. TGA analysis



**Figure S2** TGA curves of PDPP4T-1, PDPP4T-2, PDPP4T-3 and PDPP4T; heating rate: 10 °C/min. from 20 °C to 550 °C under nitrogen atmosphere.

## 4. Cyclic voltammograms



**Figure S3** Cyclic voltammograms of **PDPP4T-1**, **PDPP4T-2**, **PDPP4T-3** and **PDPP4T** (in the form of thin films) at a scan rate of  $100 \text{ mVs}^{-1}$ , with Pt as the working and counter electrodes and an Ag/AgCl electrode (saturated KCl) as the reference electrode, and  $n\text{-Bu}_4\text{NPF}_6$  (0.1 M) in  $\text{CH}_3\text{CN}$  as supporting electrolyte.

## 5. OFET device fabrication and measurements

A heavily doped  $n$ -type Si wafer with a dry oxidized  $\text{SiO}_2$  layer of 300 nm and a capacitance of  $11 \text{ nF cm}^{-2}$  was employed as the gate electrode and dielectric layer. The drain-source ( $D$ - $S$ ) gold contacts were fabricated by photo-lithography. The substrates were first cleaned by sonication in acetone and water for 5.0 min., and immersed in Piranha solution (2:1 mixture of sulfuric acid and 30% hydrogen peroxide) for 20 min. The substrates were further rinsed with deionized water and isopropyl alcohol for several times. After the substrate surfaces were modified with  $n$ -octadecyltrichlorosilane (OTS), they were washed with  $\text{CHCl}_3$ ,  $n$ -hexane and isopropyl alcohol sequentially. Next, thin films of **PDPP4T-1**, **PDPP4T-2**,

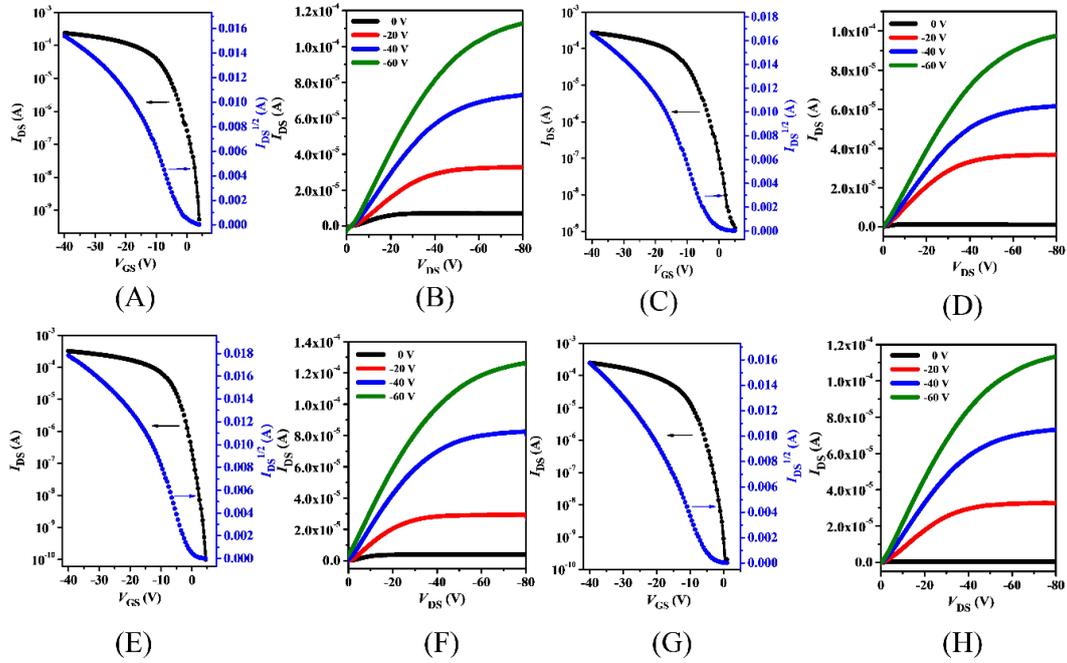
**PDPP4T-3** and **PDPP4T** were prepared by spin-coating of their hot *o*-1,2-dichlorobenzene solutions (5.0 mg/mL) onto the modified substrates at 2500 rpm for 60 s. Thin films of **PDPP4T/NMe4I** were prepared by adding a dimethyl sulfoxide (DMSO) solution of **NMe4I** to the hot *o*-1,2-dichlorobenzene (*o*-DCB) solution of **PDPP4T**, where the **PDPP4T/NMe4I** thin films were at a molar ratio of 30:1. The annealing process was performed in vacuum for 1.0 hr at 160 °C and 200 °C. The transfer and output curves of FETs were measured at room temperature in air using a Keithley 4200 SCS semiconductor parameter analyzer.

The mobilities were determined in the saturation regime by using the equation:

$$I_{DS} = \frac{W}{2L} \mu C_i (V_{GS} - V_{th})^2$$

Where  $I_{DS}$  is the drain electrode collected current;  $L$  and  $W$  are the channel length and width, respectively;  $\mu$  is the charge mobility of the device;  $C_i$  is the capacitance per unit area of the gate dielectric layer;  $V_{GS}$  and  $V_{th}$  are the gate and the threshold voltages, respectively. The  $V_{th}$  of the device was obtained by extrapolating the  $(I_{DS,sat})^{1/2}$  vs.  $V_{GS}$  plot to  $I_{DS} = 0$ .

**6. Transfer and output curves of BGBC devices with thin films of PDPP4T-1/NMe<sub>4</sub>I, PDPP4T-2/NMe<sub>4</sub>I, PDPP4T-3/NMe<sub>4</sub>I and PDPP4T/NMe<sub>4</sub>I.**

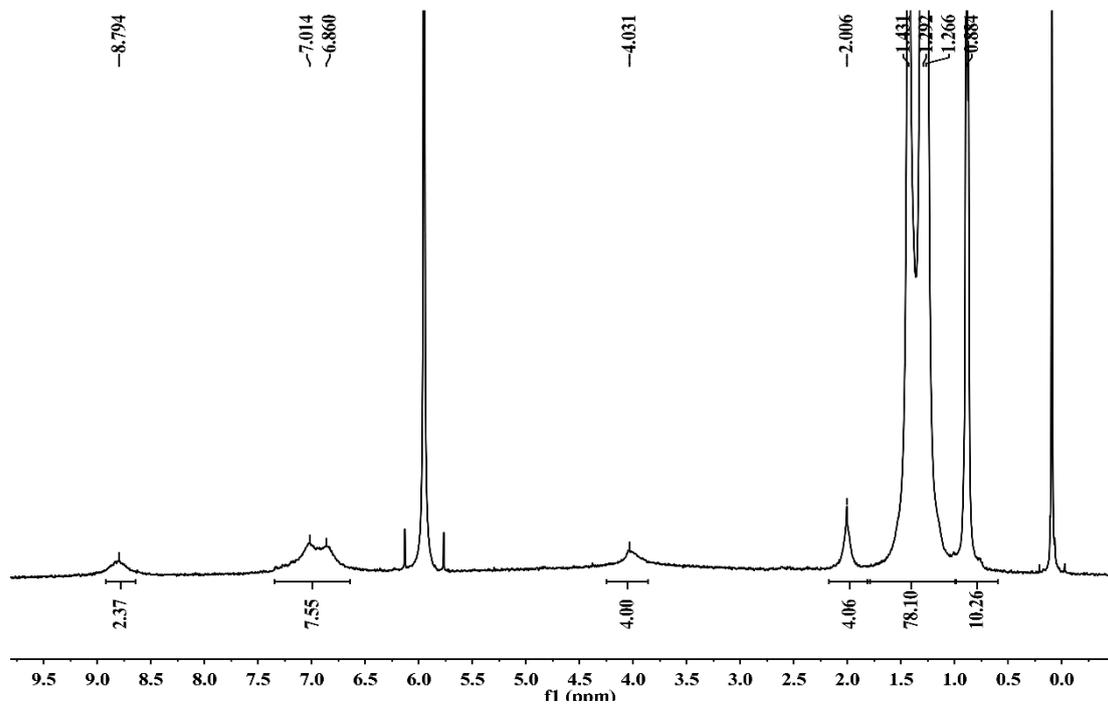


**Figure S4** The transfer and output curves of BGBC FETs with thin films of PDPP4T-1/ NMe<sub>4</sub>I (A, B), PDPP4T-2/ NMe<sub>4</sub>I (C, D), PDPP4T-3/ NMe<sub>4</sub>I (E, F) and PDPP4T/ NMe<sub>4</sub>I (G, H); the channel width ( $W$ ) and length ( $L$ ) were 1440  $\mu\text{m}$  and 50  $\mu\text{m}$ , respectively.

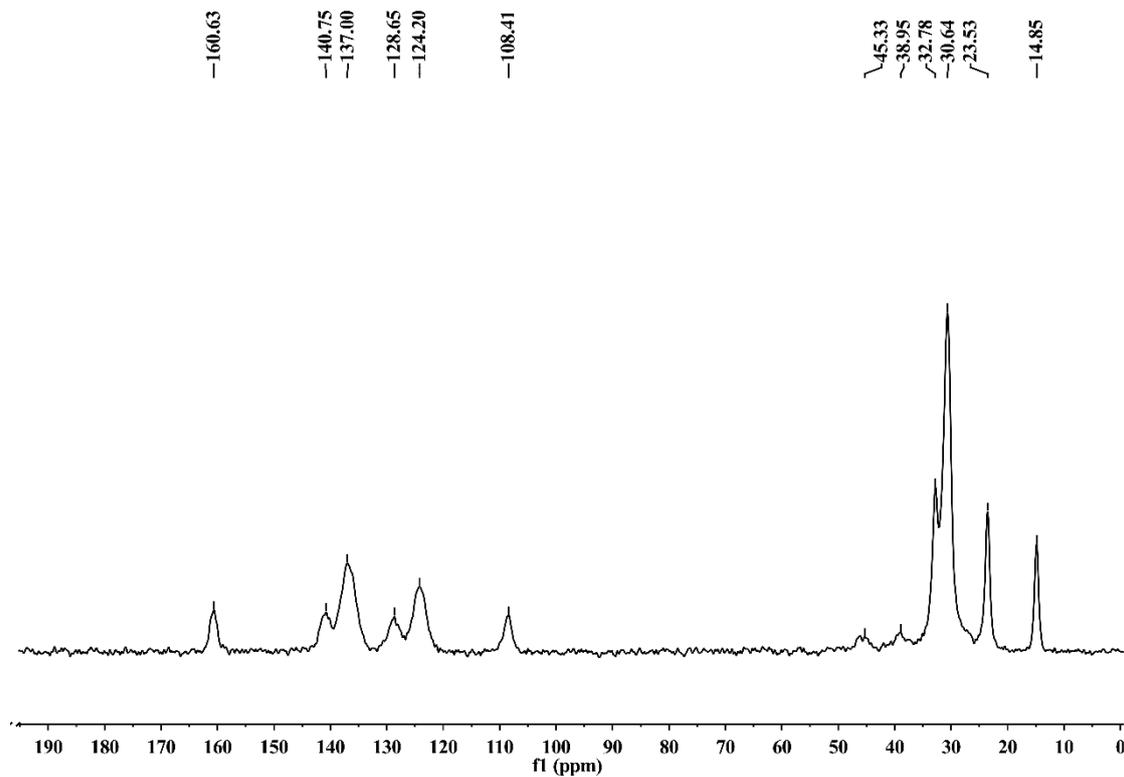
## 7. $^1\text{H}$ NMR and solid-state $^{13}\text{C}$ NMR spectra

### PDPP4T-1

#### $^1\text{H}$ NMR

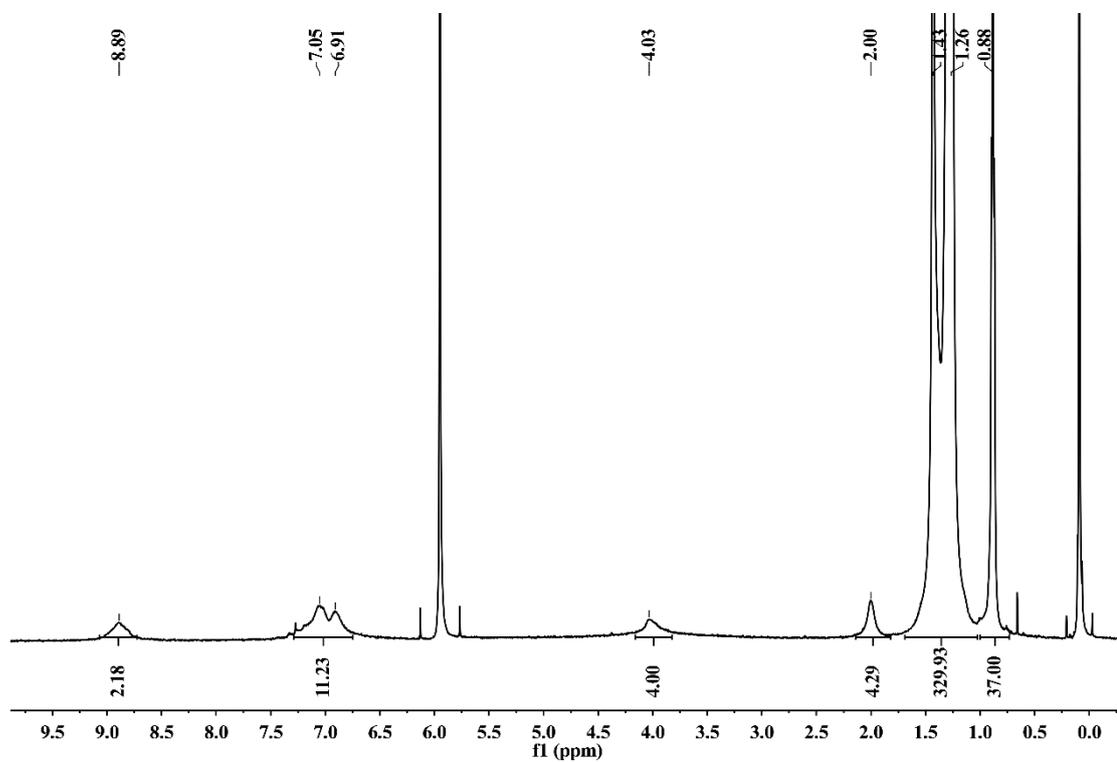


#### $^{13}\text{C}$ NMR

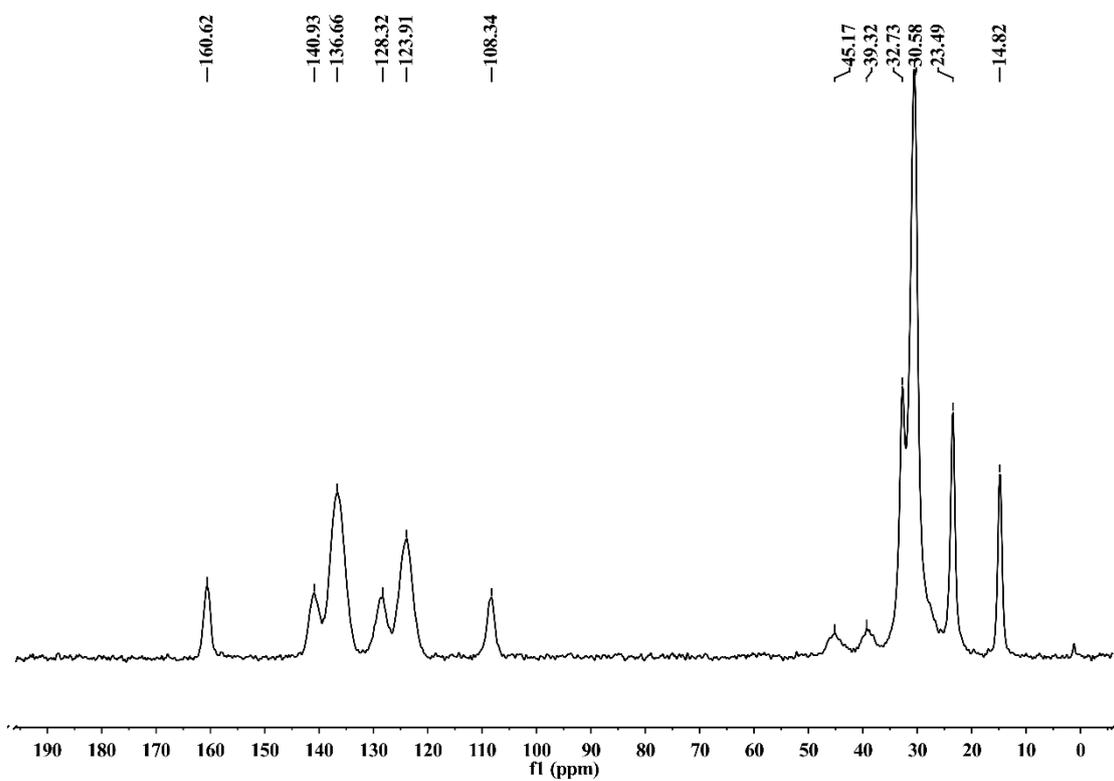


# PDPP4T-2

## <sup>1</sup>H NMR

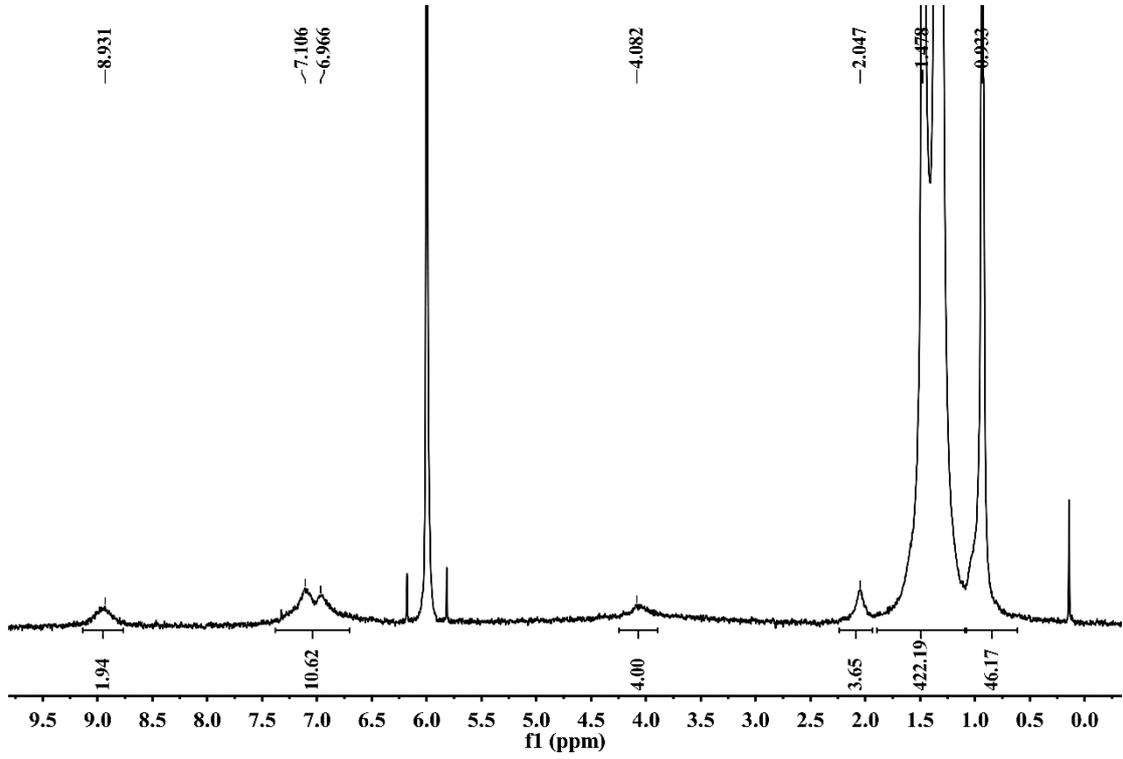


## <sup>13</sup>C NMR



**PDPP4T-3**

**<sup>1</sup>H NMR**



**<sup>13</sup>C NMR**

